Reg. No. :
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## **Question Paper Code: 46404**

## B.E. / B.Tech. DEGREE EXAMINATION, MAY 2022

Sixth Semester

Electronics and Communication Engineering								
	14UEC60	94-VLSI DE	ESIG	1				
	(Reg	ulation 201	4)					
Duration: Three hours				1	Maximum	: 100 Marks		
	Answer	ALL Ques	tions					
	(Smith char	t may be pe	ermitt	ed)				
	PART A - (	$(10 \times 1 = 10)$	Mar	ks)				
1. VLSI technology uses _	to	form integ	rated	circuit.				
(a) Transistors	(b) Switches	(c) Diodes		(d) Buffers				
2. The difficulty in achiev	ing high doping	g concentra	tion l	eads to				
<ul><li>(a) Error in concent</li><li>(c) Error in doping</li></ul>	tration		` /	rror in varia	ation			
3. In accordance to the sca	aling technolog	y, the total	delay	of the logic	e circuit de	epends on		

- - (a) The capacitor to be charged
  - (b) The voltage through which capacitance must be charged
  - (c) Available current
  - (d) All of the above

4.	In CMOS circuits, which type of power dissipation occurs due to switching of transient current & discharging of load capacitance?							
	(a) Static dissipatio	n	(b) Dynamic	dissipation				
	(c) Both a and b		(d) None of the above					
5.	The output of latches w  (a) The trigger puls  (b) Any pulse given  (c) They don't get a  (d) None of the Me	e is given to cha to go into previ any pulse more	ange the state					
6.	The sequential circuit is	also called						
	(a) Flip-flop	(b) Latch	(c) Strobe	(d) None of the Mentioned				
7.	Boundary scan test is us	sed to test						
	(a) Pins	(b) Multiplie	rs (c) Boards	(d) wires				
8.	CMOS domino logic od	ccupies						
	(a) Smaller area		(b) Larger area	ı				
9.	(c) Both of the ment Test Benches procedur		(d) None of th	e mentioned				
	(a) Smaller design		(b) Larger des	ign				
10	(c) Complicated  D. Blocking & Non blocking	ing assignment	(d) None of the	mentioned				
	<ul><li>(a) =statement &amp; ≤</li><li>(c) Statement</li></ul>	statement	(b) ≤ statement $(d)$ ≥ statement	t nt & =statement				
		PART - B (	$(5 \times 2 = 10 \text{ Marks})$					
11	. What is Body effect and	d channel Lengt	h modulation?					
12	2. Define design margin.							
13	3. Draw the pseudo nmos	inverter.						
14	What is stuck – at fault	?						
15	6. What is the structural g	ate-level model	ing?					

## PART - C (5 x 16 = 80 Marks)

16.	(a)	Explain layout design rules in detail.	(16)
		Or	
	(b)	Explain in detail about region and modes of operations in MOSFET.	(16)
17.	(b)	Explain in detail about delay estimation, logical effort and transistor sizing with example.  Or  Explain the static and dynamic power dissipation in CMOS circuits with necessa diagrams and expressions.	(16) ry (16)
18.	(a)	Explain in detail: (i) Conventional CMOS Latch (ii) Conventional CMOS Flip	flop. (16)
		Or	
	(b)	Explain in detail about sequencing dynamic circuits and synchronizers.	(16)
19.	(a)	What are the various testing methods to be considered while designing a circuit?	VLSI (16)
		Or	
	(b)	Explain in detail about silicon debug principles.	(16)
20.	(a)	Explain the concept involved in structural gate level modeling and also give description for Decoder and parity encoder.	e the (16)
		Or	
	(b)	Explain the looping statements and procedural assignments in VERILOG HDL.	(16)